



TSMC-03-442

January 22, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/714,207 11/14/03 |
Yuan-Hung Chiu et al.
A METHOD OF IN-SITU DAMAGE REMOVAL -
POST O2 DRY PROCESS
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

U.S. Patent 6,521,302 to Campana-Schmitt et al., "Method of Reducing Plasma-induced Damage," describes a method for reducing plasma induced damage to a substrate.

U.S. Patent 6,407,004 to Kimura et al., "Thin Film Device and Method for Manufacturing Thin Film Device," discusses a photoresist pattern formed on two stacked conductive layers.

U.S. Patent 5,228,950 to Webb et al., "Dry Process for Removal of Undesirable Oxide and/or Silicon Residues from Semiconductor Wafer After Processing," discloses a dry process for removing an oxide residue which involves a plasma etch including NF₃ and optionally a reactive gas or an inert gas in combination with applied magnetic field of 25 to 150 Gauss.

U.S. Patent 6,319,842 to Khosla et al., "Method of Cleansing Vias in Semiconductor Wafer Having Metal Conductive Layer," describes a method of cleaning vias in which non-volatile residues are first removed by sputtering with an inert gas plasma.

Sincerely,

A handwritten signature in black ink, appearing to read 'S. B. Ackerman', written over a horizontal line.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

Doctor Number (Cp-00000000)

Application Number

TSmc-03-442

10/714, 207

Appelcon!

Yuan-Hung Chin et al.

FDing Date

11/14/03

Group Art Unit

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

[illegible]

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.